

## N-Channel 30-V (D-S) MOSFET

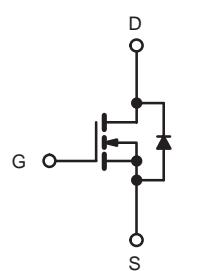
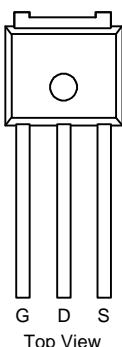
PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
30	0.07 at $V_{GS} = 10$ V	53	19 nC
	0.09 at $V_{GS} = 4.5$ V	48	

### FEATURES

- Halogen-free
- TrenchFET® Gen III Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested


 RoHS  
 COMPLIANT

TO-251



N-Channel MOSFET

Top View

### APPLICATIONS

- DC/DC Conversion
  - System Power

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current	$I_{DM}$	165	
Avalanche Current	$I_{AS}$	25	
Avalanche Energy	$E_{AS}$	40	
Continuous Source-Drain Diode Current	$I_S$	15	
		2.9 <sup>b, c</sup>	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	$R_{thJA}$	29	36	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	3.6	

Notes:

- Based on  $T_C = 25$  °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$  s.

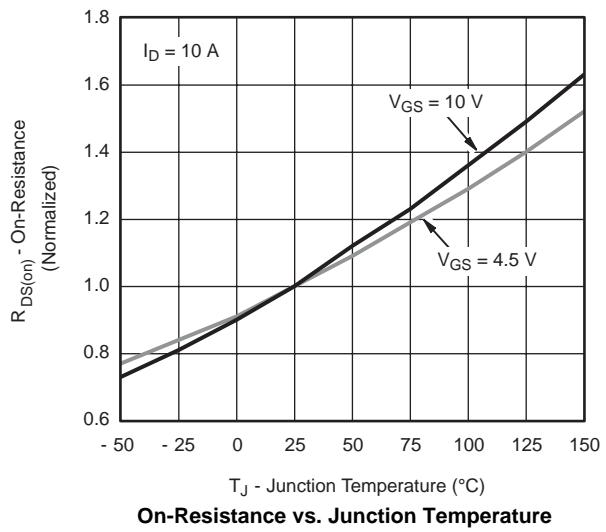
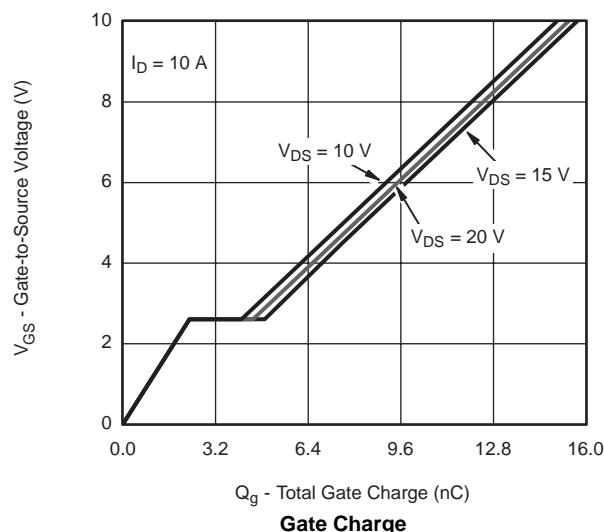
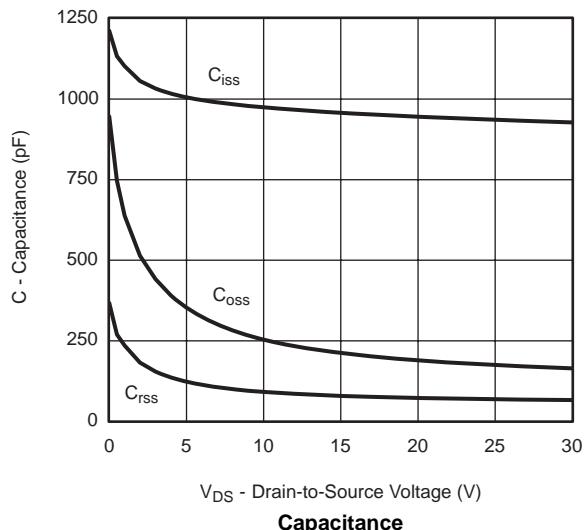
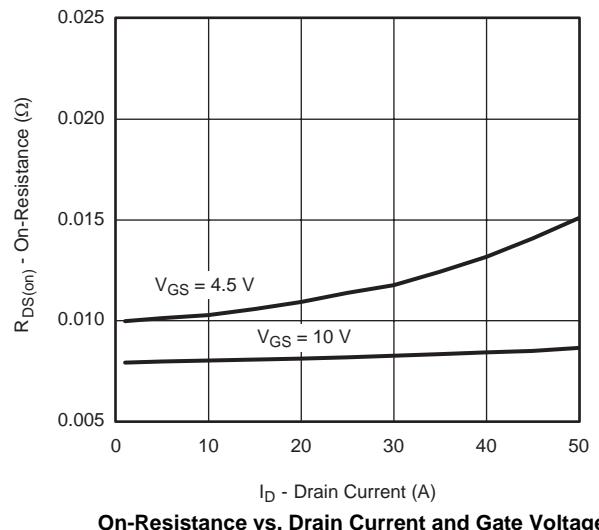
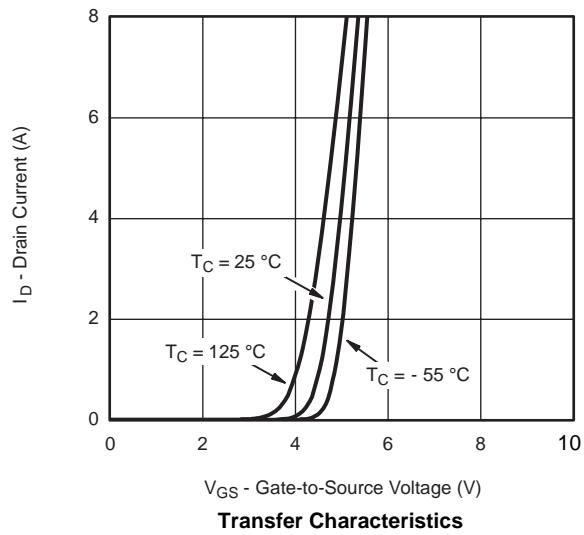
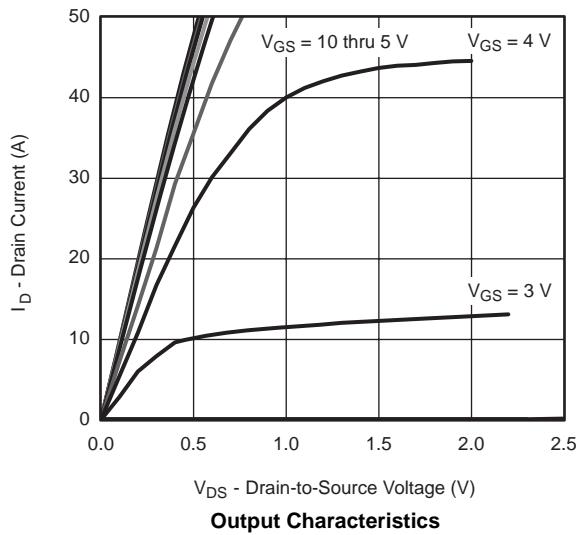
**SPECIFICATIONS**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

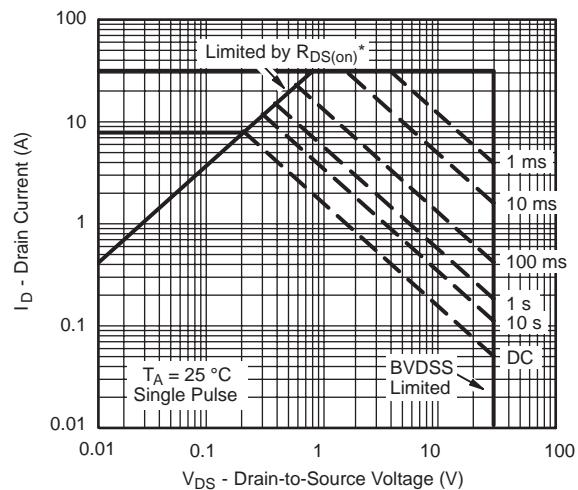
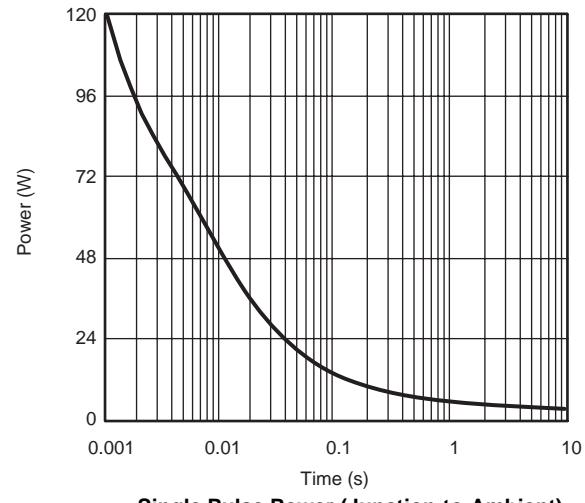
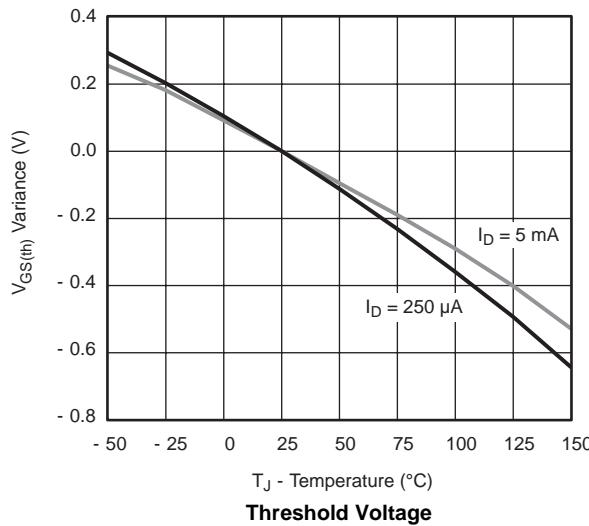
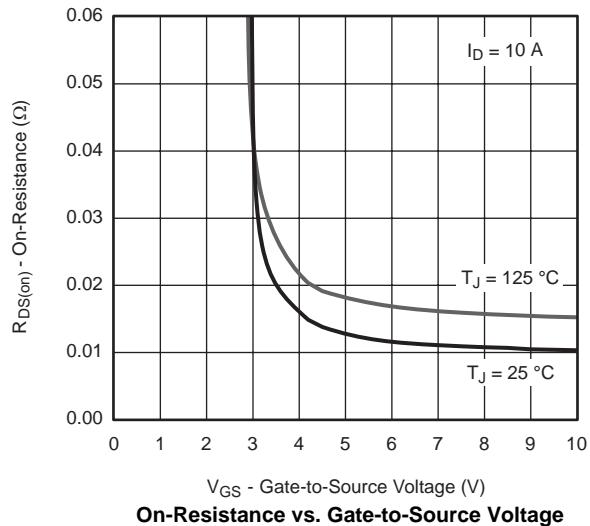
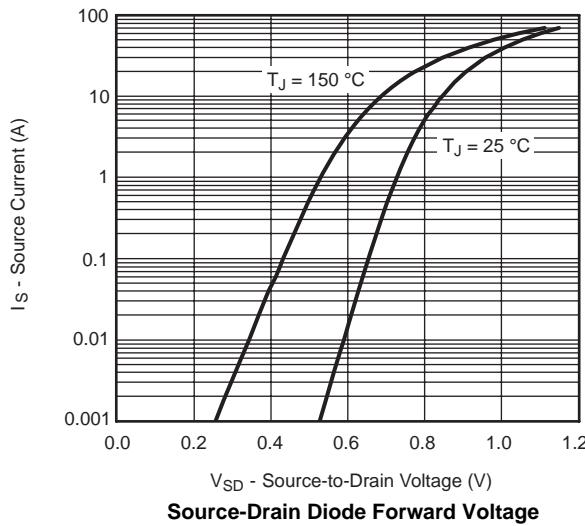
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	30			V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		33		$\text{mV}/^\circ\text{C}$	
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			-5			
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	1.2		3.0	V	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$	
		$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$			5		
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$ , $V_{GS} = 10 \text{ V}$	15			A	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$		0.070		$\Omega$	
		$V_{GS} = 4.5 \text{ V}$ , $I_D = 7 \text{ A}$		0.090			
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 10 \text{ A}$		24		S	
<b>Dynamic<sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		1400		$\text{pF}$	
Output Capacitance	$C_{oss}$			200			
Reverse Transfer Capacitance	$C_{rss}$			150			
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$		33		$\text{nC}$	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 10 \text{ A}$		18			
Gate-Drain Charge	$Q_{gd}$			7.3			
Gate Resistance	$R_g$		$f = 1 \text{ MHz}$	6.2			
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$ , $R_L = 1.5 \Omega$ $I_D \geq 10 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$ , $R_g = 1 \Omega$		0.2	0.8	1.6	$\Omega$
Rise Time	$t_r$				15	30	$\text{ns}$
Turn-Off Delay Time	$t_{d(\text{off})}$				12	24	
Fall Time	$t_f$				13	26	
Turn-On Delay Time	$t_{d(\text{on})}$				10	20	
Rise Time	$t_r$				9	18	
Turn-Off Delay Time	$t_{d(\text{off})}$				9	18	
Fall Time	$t_f$				14	28	
					8	16	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			16	$\text{A}$	
Pulse Diode Forward Current	$I_{SM}$				32		
Body Diode Voltage	$V_{SD}$	$I_S = 3 \text{ A}$ , $V_{GS} = 0 \text{ V}$		0.78	1.2	V	
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10 \text{ A}$ , $dl/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$		17	34	$\text{ns}$	
Body Diode Reverse Recovery Charge	$Q_{rr}$			9.5	19	$\text{nC}$	
Reverse Recovery Fall Time	$t_a$			10		$\text{ns}$	
Reverse Recovery Rise Time	$t_b$			7			

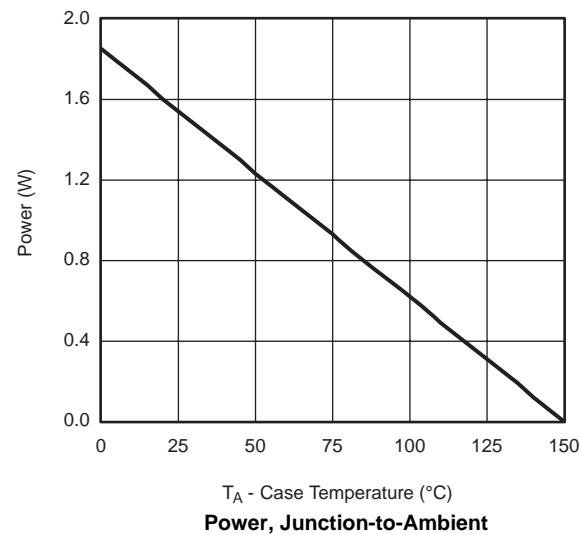
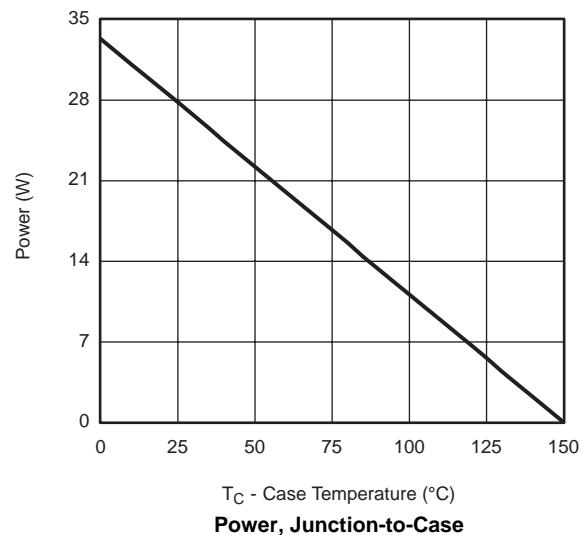
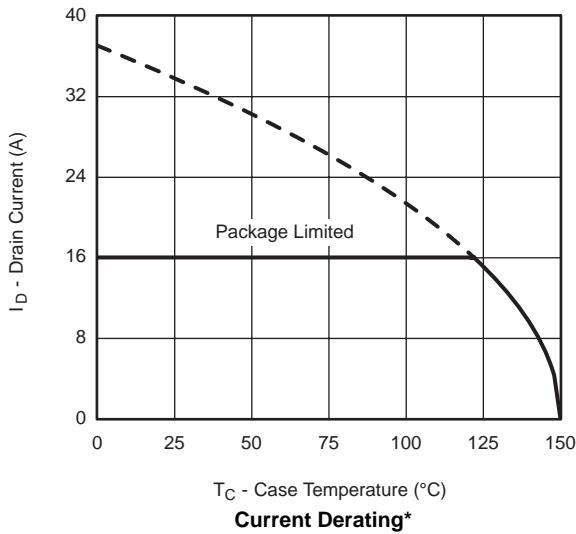
Notes:

a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

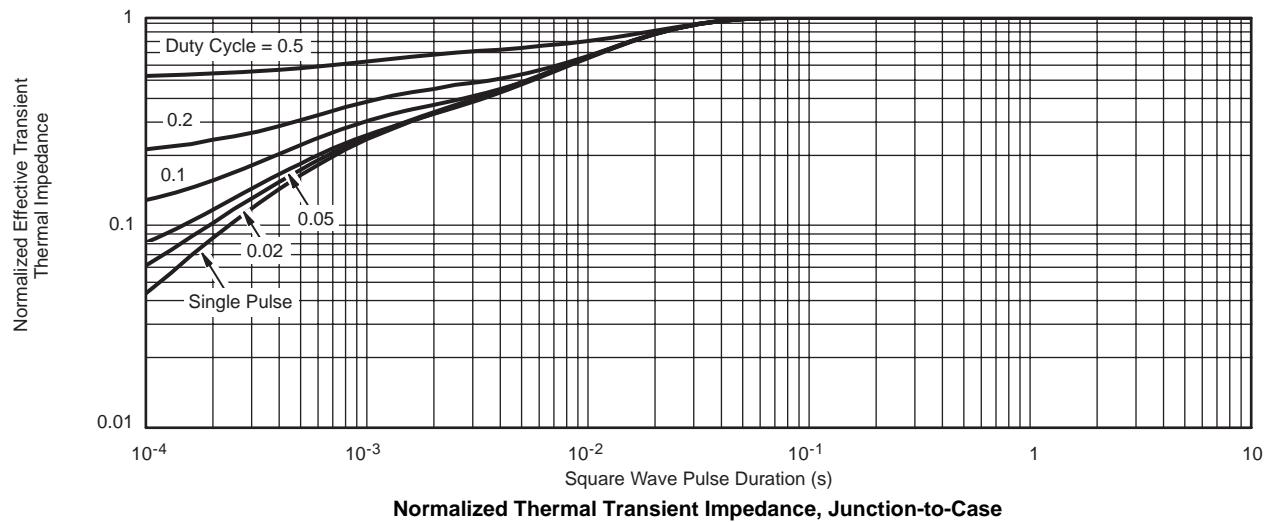
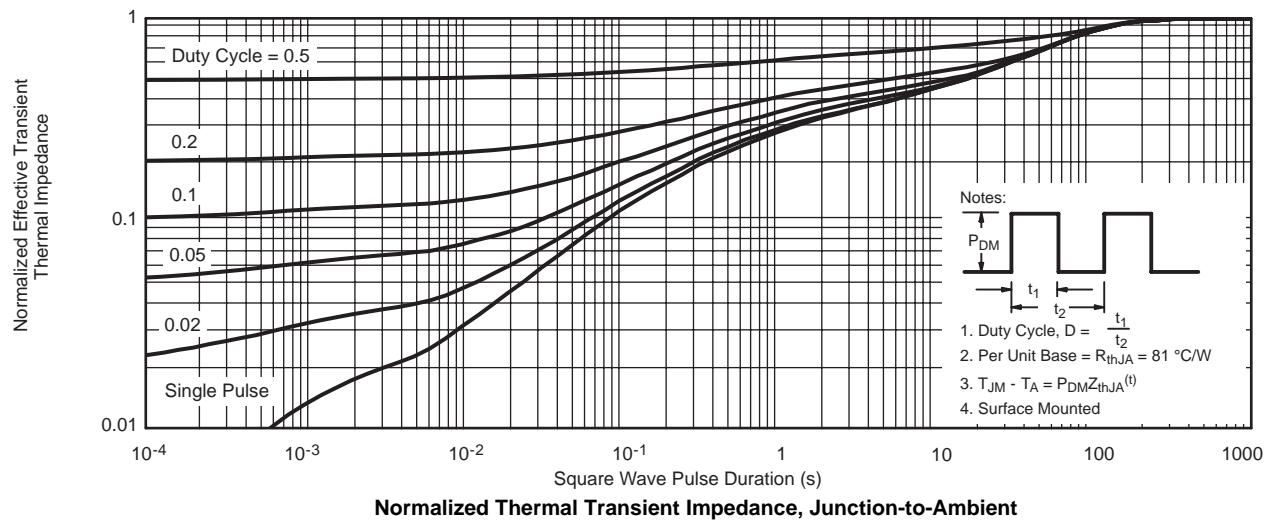
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


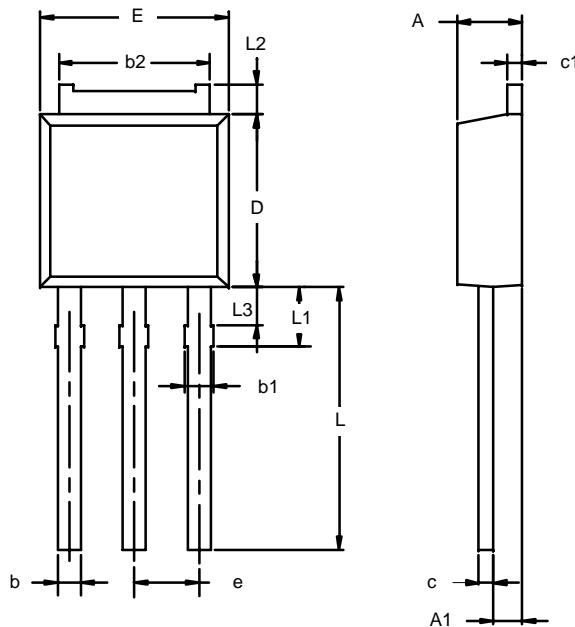
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\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


## TO-251AA (DPAK)



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	3.89	9.53	0.153	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060

ECN: S-03946—Rev. E, 09-Jul-01  
 DWG: 5346

Note: Dimension L3 is for reference only.

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